

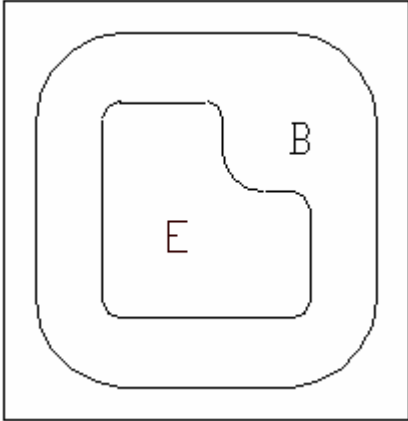
9015B Silicon PNP Epitaxial Transistor

Description :The 9015B is designed for use in pre-amplifier of low level and low noise

Features: ●Excellent h_{FE} Linearity

●Complementary to 9014B

Chip Appearance

	Chip Size		350um × 350um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	100um × 100um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		40um
	Wafer Size		6 inch

Electrical Characteristics($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1\text{mA}$,	-50		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}$,	-45		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1\text{mA}$,	-5.0		V
DC Current Gain	h_{FE}	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	150	600	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-5\text{mA}$		-0.3	V